74AUP1Z04-Q100

Low-power X-tal driver with enable and internal resistor

Rev. 2 — 27 January 2022

Product data sheet

1. General description

The 74AUP1Z04-Q100 is a crystal driver with enable and internal resistor. When not in use the $\overline{\text{EN}}$ input can be driven HIGH, putting the device in a low power disable mode with X1 pulled HIGH via R_{PU}, X2 set LOW and Y set HIGH. Schmitt trigger action on the $\overline{\text{EN}}$ input makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V. Schmitt-trigger action at all inputs makes the circuit tolerant of slower input rise and fall times.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Wide supply voltage range from 0.8 V to 3.6 V
- · CMOS low power dissipation
- · High noise immunity
- Overvoltage tolerant inputs to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation at output Y
- Latch-up performance exceeds 100 mA per JESD78B Class II
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.65 V to 1.95 V)
 - JESD8-5 (2.3 V to 2.7 V)
 - JESD8C (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V

3. Ordering information

Table 1. Ordering information

Type number	Package	Package Package						
	Temperature range	Name	Description	Version				
74AUP1Z04GW-Q100	-40 °C to +125 °C		plastic thin shrink small outline package; 6 leads; body width 1.25 mm	SOT363-2				



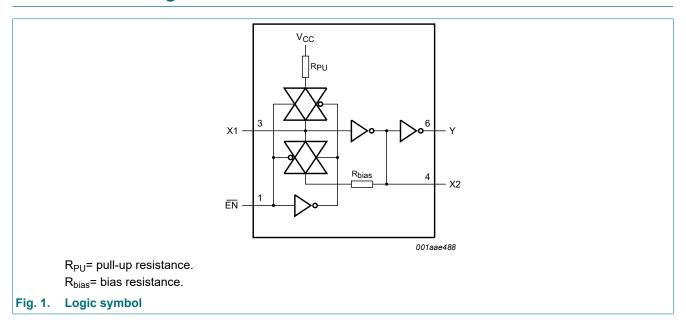
4. Marking

Table 2. Marking

Type number	Marking code [1]
74AUP1Z04GW-Q100	a4

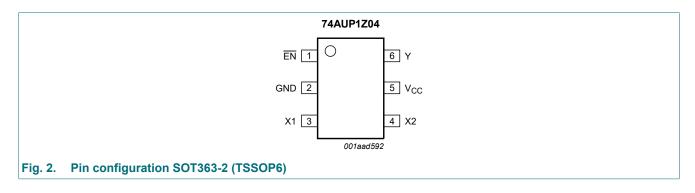
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1. Pinning



6.2. Pin description

Table 3. Pin description

Symbol	Pin	Description
EN	1	enable input (active LOW)
GND	2	ground (0 V)
X1	3	data input
X2	4	data output
V _{CC}	5	supply voltage
Υ	6	data output

7. Functional description

Table 4. Function table

 $H = HIGH \ voltage \ level; \ L = LOW \ voltage \ level.$

Input		Output		
EN	X1	X2	Υ	
L	L	Н	L	
L	Н	L	Н	
Н	L	Н	L	
Н	Н	L	Н	

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage	[1]	-0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	[1]	-0.5	V _{CC} + 0.5	V
Io	output current	$V_O = 0 \text{ V to } V_{CC}$	-	±20	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C to} + 125 ^{\circ}\text{C}$ [2]	-	250	mW

^[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

^[2] For SOT363-2 (TSSOP6) package: P_{tot} derates linearly with 3.7 mW/K above 83 °C.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage		0	V _{CC}	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 0.8 V to 3.6 V	-	200	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C		-1		I	
V _{IH}	HIGH-level input voltage	X1 input				
		V _{CC} = 0.8 V to 3.6 V	0.75 × V _{CC}	-	-	V
		EN input				
		V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	X1 input				
		V _{CC} = 0.8 V to 3.6 V	-	-	0.25 × V _{CC}	V
		EN input				
		V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OH}	HIGH-level output	Y output; V _I at X1 input = V _{IH} or V _{IL}				
	voltage	I_{O} = -20 μ A; V_{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.75 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.11	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.32	-	-	V
		I_{O} = -2.3 mA; V_{CC} = 2.3 V	2.05	-	-	V
		I_{O} = -3.1 mA; V_{CC} = 2.3 V	1.9	-	-	V
		I_{O} = -2.7 mA; V_{CC} = 3.0 V	2.72	-	-	V
		I_{O} = -4.0 mA; V_{CC} = 3.0 V	2.6	-	-	V
		X2 output; V _I = GND or V _{CC}				
		I_{O} = -20 μ A; V_{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.75 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.11	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.32	-	-	V
		I_{O} = -2.3 mA; V_{CC} = 2.3 V	2.05	-	-	V
		I_{O} = -3.1 mA; V_{CC} = 2.3 V	1.9	-	-	V
		I_{O} = -2.7 mA; V_{CC} = 3.0 V	2.72	-	-	V
		I_{O} = -4.0 mA; V_{CC} = 3.0 V	2.6	-	-	V
V _{OL}	LOW-level output	Y output; V _I at X1 input = V _{IH} or V _{IL}				
	voltage	I_{O} = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V	-	-	0.31	V
		I_{O} = 3.1 mA; V_{CC} = 2.3 V	-	-	0.44	V
		I_{O} = 2.7 mA; V_{CC} = 3.0 V	-	-	0.31	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
		X2 output; V _I = GND or V _{CC}				
		I_{O} = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V	-	-	0.31	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V
		I_{O} = 2.7 mA; V_{CC} = 3.0 V	-	-	0.31	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.44	V

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
l _l	input leakage current	X1 input				
		$V_I = \overline{EN} = V_{CC}$; $V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.1	μA
		EN input				
		V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.1	μA
I _{pu}	pull-up current	X1 input; EN = V _{CC}				
		V _I = GND; V _{CC} = 0.8 V to 3.6 V	-	-	15	μA
I _{OFF}	power-off leakage current	$V_1 \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V}; V_{CC} = 0 \text{ V}$ [1]	-	-	±0.2	μΑ
Δl _{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V [1]	-	-	±0.2	μΑ
I _{CC}	supply current	V_I = GND or V_{CC} ; I_O = 0 A; \overline{EN} = GND; V_{CC} = 0.8 V to 3.6 V	-	-	75	μΑ
Δl _{CC}	additional supply current	EN input				
		$V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	40	μA
Cı	input capacitance	X1 input				
		V_{CC} = 0 V to 3.6 V; V_{I} = GND or V_{CC}	-	1.3	-	pF
		EN input				
		V_{CC} = 0 V to 3.6 V; V_{I} = GND or V_{CC}	-	0.8	-	pF
Co	output capacitance	X2 output				
		V _O = GND; V _{CC} = 0 V	-	1.5	-	pF
		Y output				
		V _O = GND; V _{CC} = 0 V	-	1.7	-	pF
9 _{fs}	forward	see Fig. 8 and Fig. 9				
	transconductance	V _{CC} = 0.8 V	-	-	-	mA/V
		V _{CC} = 1.1 V to 1.3 V	0.2	-	9.9	mA/V
		V _{CC} = 1.4 V to 1.6 V	3.9	-	17.7	mA/V
		V _{CC} = 1.65 V to 1.95 V	7.9	-	24.3	mA/V
		V _{CC} = 2.3 V to 2.7 V	18	-	30.7	mA/V
		V _{CC} = 3.0 V to 3.6 V	20.5	-	32.4	mA/V
R _{bias}	bias resistance	\overline{EN} = GND; f_i = 0 Hz; V_I = 0 V or V_{CC} ; see $\underline{Fig. 3}$; for frequency behavior see $\underline{Fig. 4}$	1.08	1.62	3.08	ΜΩ
T _{amb} = -4	40 °C to +85 °C					
V _{IH}	HIGH-level input voltage	X1 input				
		V _{CC} = 0.8 V to 3.6 V	0.75 × V _{CC}	-	-	V
		EN input				
		V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V

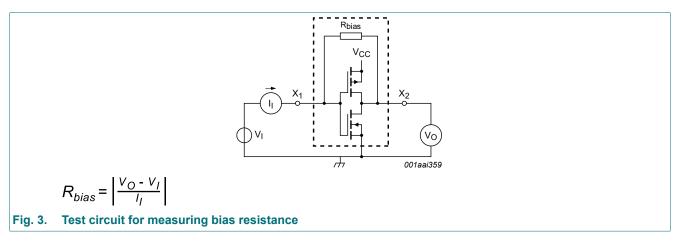
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{IL}	LOW-level input voltage	X1 input				
		V _{CC} = 0.8 V to 3.6 V	-	-	0.25 × V _{CC}	V
		EN input				
		V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	٧
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
′он	HIGH-level output	Y output; V _I at X1 input = V _{IH} or V _{IL}				
	voltage	$I_O = -20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.7 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.03	-	-	٧
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.30	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	1.97	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.85	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.67	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.55	-	-	V
		V _I at X1 input = V _{IH} or V _{IL}				
		$I_O = -20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.7 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.03	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.30	_	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	1.97	_	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.85	_	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.67	_	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.55	-	-	V
o _L	LOW-level output	Y output; V _I at X1 input = V _{IH} or V _{IL}				
02	voltage	I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	_	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	_	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	_	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	_	0.35	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.33	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.33	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	_	-	0.45	V
		X2 output; V _I = GND or V _{CC}				
		$I_O = 20 \mu A; V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	_	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	_	_	0.3 × V _{CC}	V
		$I_{O} = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	_	0.37	V
		$I_O = 1.9 \text{ mA}$; $V_{CC} = 1.65 \text{ V}$	-	_	0.35	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	_	0.33	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	_	0.45	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	_	0.33	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	_	_	0.45	V

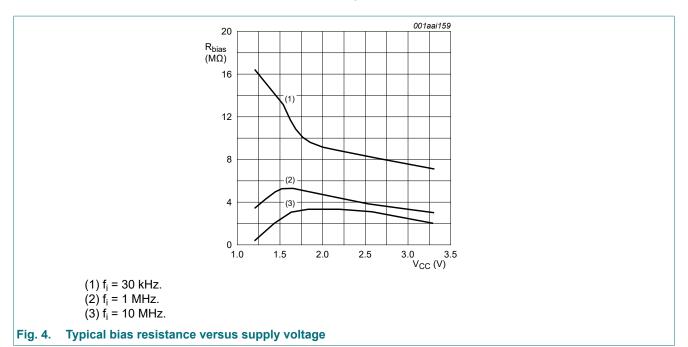
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _I	input leakage current	X1 input				
		$V_I = \overline{EN} = V_{CC}$; $V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.5	μΑ
		EN input				
		V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.5	μA
I _{pu}	pull-up current	X1 input; EN = V _{CC}			±0.5 ±0.5 15 ±0.5 ±0.6 75 50 - 10.8 21.2 29.9 38.0 39.2 3.11	
		V _I = GND; V _{CC} = 0.8 V to 3.6 V	-	-	15	μΑ
I _{OFF}	power-off leakage current	$V_1 \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V}; V_{CC} = 0 \text{ V}$ [1]	-	-	±0.5	μΑ
Δl _{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ [1] $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.6	μΑ
I _{CC}	supply current	V_I = GND or V_{CC} ; I_O = 0 A; \overline{EN} = GND; V_{CC} = 0.8 V to 3.6 V	-	-	75	μΑ
ΔI _{CC}	additional supply current	EN input			±0.5 ±0.5 15 ±0.5 ±0.6 75 50 - 10.8 21.2 29.9 38.0 39.2 3.11	
		$V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	50	μΑ
g _{fs}	forward	see <u>Fig. 8</u> and <u>Fig. 9</u>				
	transconductance	V _{CC} = 0.8 V	-		-	mA/V
		V _{CC} = 1.1 V to 1.3 V	-	-	10.8	mA/V
		V _{CC} = 1.4 V to 1.6 V	1.8	-	21.2	mA/V
		V _{CC} = 1.65 V to 1.95 V	7.5	-	29.9	mA/V
		V _{CC} = 2.3 V to 2.7 V	15.0	-	38.0	mA/V
		V _{CC} = 3.0 V to 3.6 V	17.8	-	39.2	mA/V
R _{bias}	bias resistance	$\overline{\text{EN}}$ = GND; f_i = 0 Hz; V_l = 0 V or V_{CC} ; see $\overline{\text{Fig. 3}}$; for frequency behavior see $\overline{\text{Fig. 4}}$	1.07	-	3.11	ΜΩ
T _{amb} = -4	40 °C to +125 °C					
V _{IH}	HIGH-level input voltage	X1 input				
		V _{CC} = 0.8 V to 3.6 V	0.75 × V _{CC}	-	-	V
		EN input				
		V _{CC} = 0.8 V	0.75 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	X1 input				
		V _{CC} = 0.8 V to 3.6 V	-	-	0.25 × V _{CC}	V
		EN input				
		V _{CC} = 0.8 V	-	-	0.25 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OH}	HIGH-level output	Y output; V _I at X1 input = V _{IH} or V _{IL}				V
	voltage	I_{O} = -20 μ A; V_{CC} = 0.8 V to 3.6 V	V _{CC} - 0.11	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.6 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	0.93	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.17	-	-	V
		I_{O} = -2.3 mA; V_{CC} = 2.3 V	1.77	-	-	V
		I_{O} = -3.1 mA; V_{CC} = 2.3 V	1.67	-	-	V
		I_{O} = -2.7 mA; V_{CC} = 3.0 V	2.40	-	-	V
		I_{O} = -4.0 mA; V_{CC} = 3.0 V	2.30	-	-	V
		X2 output; V _I = GND or V _{CC}				V
		$I_O = -20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	V _{CC} - 0.11	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.6 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	0.93	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.17	-	-	V
		I_{O} = -2.3 mA; V_{CC} = 2.3 V	1.77	-	-	V
		I_{O} = -3.1 mA; V_{CC} = 2.3 V	1.67	-	-	V
		I_{O} = -2.7 mA; V_{CC} = 3.0 V	2.40	-	-	V
		I_{O} = -4.0 mA; V_{CC} = 3.0 V	2.30	-	-	V
/ _{OL}	LOW-level output	Y output; V _I at X1 input = V _{IH} or V _{IL}				
	voltage	$I_O = 20 \mu A; V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.33 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V	-	-	0.36	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.50	V
		I_{O} = 2.7 mA; V_{CC} = 3.0 V	-	-	0.36	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.50	V
		X2 output; V _I = GND or V _{CC}				
		$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.33 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	_	0.39	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.36	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.50	٧
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.36	٧
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	_	0.50	V

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _I	input leakage current	X1 input					
		$V_I = \overline{EN} = V_{CC}$; $V_{CC} = 0 \text{ V to } 3.6 \text{ V}$		-	-	±0.75	μA
		EN input					
		V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V		-	-	±0.75	μA
I _{pu}	pull-up current	X1 input; EN = V _{CC}					
		V _I = GND; V _{CC} = 0.8 V to 3.6 V		-	-	15	μA
I _{OFF}	power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V}; V_{CC} = 0 \text{ V}$ [1]]	-	-	±0.75	μΑ
Δl _{OFF}	additional power-off leakage current	$V_1 \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V};$ [1] $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$]	-	-	±0.75	μΑ
I _{CC}	supply current	V_I = GND or V_{CC} ; I_O = 0 A; \overline{EN} = GND; V_{CC} = 0.8 V to 3.6 V		-	-	75	μΑ
ΔI_{CC}	additional supply current	EN input					
		$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$		-	-	75	μA
g _{fs}	forward	see Fig. 8 and Fig. 9					
	transconductance	V _{CC} = 0.8 V		-	-	-	mA/V
		V _{CC} = 1.1 V to 1.3 V		-	-	10.8	mA/V
		V _{CC} = 1.4 V to 1.6 V		1.8	-	21.2	mA/V
		V _{CC} = 1.65 V to 1.95 V		6.9	-	29.9	mA/V
		V _{CC} = 2.3 V to 2.7 V		13.4	-	38.0	mA/V
		V _{CC} = 3.0 V to 3.6 V		15.8	-	39.2	mA/V
R _{bias}	bias resistance	EN = GND; f _i = 0 Hz; V _I = 0 V or V _{CC} ; see Fig. 3; for frequency behavior see Fig. 4		1.07	-	3.11	ΜΩ

[1] Only for output Y and input $\overline{\text{EN}}$.





11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 7.

Symbol	Parameter	ter Conditions		T _{amb} = 25 °C			T _{amb} = -40 °C to +85 °C		T _{amb} = -40 °C to +125 °C	
			Min	Typ [1]	Max	Min	Max	Min	Max	
C _L = 5 pl	F									
t _{pd}	propagation	X1 to X2; see <u>Fig. 5</u> [2]								
	delay	V _{CC} = 0.8 V	-	12.8	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	1.2	3.0	3.9	1.2	3.9	1.2	3.9	ns
		V _{CC} = 1.4 V to 1.6 V	1.0	2.2	2.6	1.0	2.7	1.0	2.7	ns
		V _{CC} = 1.65 V to 1.95 V	0.8	1.9	2.3	0.8	2.4	0.8	2.5	ns
		V _{CC} = 2.3 V to 2.7 V	0.7	1.6	1.9	0.7	2.0	0.7	2.0	ns
		V _{CC} = 3.0 V to 3.6 V	0.7	1.4	1.6	0.7	1.7	0.7	1.7	ns
		X1 to Y; see <u>Fig. 6</u> [2]								
		V _{CC} = 0.8 V	-	39.2	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.5	8.0	10.7	2.3	10.8	2.3	10.9	ns
		V _{CC} = 1.4 V to 1.6 V	2.2	5.5	6.6	2.0	7.0	2.0	7.0	ns
		V _{CC} = 1.65 V to 1.95 V	1.8	4.4	5.5	1.7	5.9	1.7	6.0	ns
		V _{CC} = 2.3 V to 2.7 V	1.5	3.5	4.1	1.4	4.4	1.4	4.5	ns
		V _{CC} = 3.0 V to 3.6 V	1.5	3.1	3.5	1.4	3.8	1.4	3.8	ns

Symbol	Parameter	meter Conditions	T,	T _{amb} = 25 °C			T _{amb} = -40 °C to +85 °C		T _{amb} = -40 °C to +125 °C	
			Min	Typ [1]	Max	Min	Max	Min	Max	
C _L = 10	pF		'							
	propagation	X1 to X2; see <u>Fig. 5</u> [2]								
	delay	V _{CC} = 0.8 V	-	20.9	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	1.4	4.1	5.4	1.3	5.6	1.3	5.6	ns
		V _{CC} = 1.4 V to 1.6 V	1.3	2.9	3.6	1.2	3.8	1.2	3.8	ns
		V _{CC} = 1.65 V to 1.95 V	1.2	2.5	3.0	1.1	3.2	1.1	3.2	ns
		V _{CC} = 2.3 V to 2.7 V	0.9	2.0	2.4	8.0	2.5	0.8	2.5	ns
		V _{CC} = 3.0 V to 3.6 V	0.9	1.8	2.1	8.0	2.3	8.0	2.3	ns
		X1 to Y; see <u>Fig. 6</u> [2]								
		V _{CC} = 0.8 V	-	46.6	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.7	9.2	12.4	2.5	12.7	2.5	12.7	ns
		V _{CC} = 1.4 V to 1.6 V	2.5	6.3	7.8	2.2	8.2	2.2	8.2	ns
		V _{CC} = 1.65 V to 1.95 V	2.3	5.0	6.2	2.2	6.7	2.2	6.7	ns
		V _{CC} = 2.3 V to 2.7 V	1.8	4.0	4.7	1.7	5.0	1.7	5.1	ns
		V _{CC} = 3.0 V to 3.6 V	1.9	3.6	4.2	1.8	4.5	1.8	4.5	ns
C _L = 15	pF				'					
t _{pd}	propagation	X1 to X2; see <u>Fig. 5</u> [2]								
	delay	V _{CC} = 0.8 V	-	28.9	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	1.7	5.2	7.1	1.6	7.2	1.6	7.3	ns
		V _{CC} = 1.4 V to 1.6 V	1.6	3.6	4.4	1.6	4.7	1.6	4.8	ns
		V _{CC} = 1.65 V to 1.95 V	1.3	3.0	3.7	1.3	3.9	1.3	4.0	ns
		V _{CC} = 2.3 V to 2.7 V	1.0	2.4	2.9	1.0	3.1	1.0	3.1	ns
		V _{CC} = 3.0 V to 3.6 V	1.1	2.2	2.5	1.0	2.7	1.0	2.7	ns
		X1 to Y; see <u>Fig. 6</u> [2]								
		V _{CC} = 0.8 V	-	53.9	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.1	10.4	14.2	2.8	14.6	2.8	14.7	ns
		V _{CC} = 1.4 V to 1.6 V	2.9	7.0	8.5	2.7	9.2	2.7	9.3	ns
		V _{CC} = 1.65 V to 1.95 V	2.5	5.6	6.9	2.3	7.4	2.3	7.5	ns
		V _{CC} = 2.3 V to 2.7 V	2.1	4.5	5.4	2.0	5.7	2.0	5.7	ns
		V _{CC} = 3.0 V to 3.6 V	2.3	4.1	4.7	2.1	5.1	2.1	5.1	ns

Symbol	Parameter	meter Conditions		T _{amb} = 25 °C			-40 °C 35 °C	T _{amb} = -40 °C to +125 °C		Unit
			Min	Typ [1]	Max	Min	Max	Min	Max	
C _L = 30	pF									
t _{pd}	propagation	X1 to X2; see <u>Fig. 5</u> [2]								
	delay	V _{CC} = 0.8 V	-	52.8	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.4	8.5	11.8	2.3	12.2	2.3	12.4	ns
		V _{CC} = 1.4 V to 1.6 V	2.2	5.6	6.8	2.0	7.5	2.0	7.6	ns
		V _{CC} = 1.65 V to 1.95 V	2.0	4.5	5.6	1.9	6.2	1.9	6.2	ns
		V _{CC} = 2.3 V to 2.7 V	1.5	3.7	4.2	1.4	4.6	1.4	4.6	ns
		V _{CC} = 3.0 V to 3.6 V	1.7	3.3	3.7	1.6	4.0	1.6	4.2	ns
		X1 to Y; see <u>Fig. 6</u> [2]								
		V _{CC} = 0.8 V	-	77.6	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.7	13.8	19.2	3.3	19.8	3.3	20.1	ns
		V _{CC} = 1.4 V to 1.6 V	3.4	9.2	11.2	3.1	12.2	3.1	12.3	ns
		V _{CC} = 1.65 V to 1.95 V	3.4	7.4	8.8	3.1	9.7	3.1	9.7	ns
		V _{CC} = 2.3 V to 2.7 V	2.6	5.9	6.7	2.4	7.4	2.4	7.4	ns
		V _{CC} = 3.0 V to 3.6 V	3.2	5.4	6.2	2.9	6.7	2.9	6.9	ns
C _L = 5 p	F, 10 pF, 15 p	F and 30 pF		1	'	,			'	
C _{PD}	power dissipation	$f_i = 1 \text{ MHz}; \overline{EN} = \text{GND};$ [3][4][5] $V_I = \text{GND to } V_{CC}$								
	capacitance	V _{CC} = 0.8 V	-	6.8	-	-	-	-	-	pF
		V _{CC} = 1.1 V to 1.3 V	-	12.0	-	-	-	-	-	pF
		V _{CC} = 1.4 V to 1.6 V	-	18.2	-	-	-	-	-	pF
		V _{CC} = 1.65 V to 1.95 V	-	19.2	-	-	-	-	-	pF
		V _{CC} = 2.3 V to 2.7 V	-	21.9	-	-	-	-	-	pF
		V _{CC} = 3.0 V to 3.6 V	-	24.9	-	-	-	-	-	pF

- [1] All typical values are measured at nominal V_{CC} .
- t_{pd} is the same as t_{PLH} and t_{PHL} .
- All specified values are the average typical values over all stated loads.
- [4] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W). $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$$
 where

 f_i = input frequency in MHz;

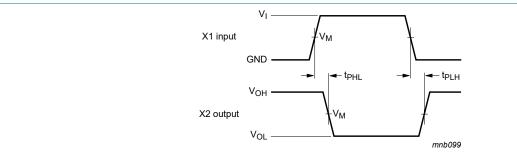
f_o = output frequency in MHz;

C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching; $\Sigma(C_L \times V_{CC}^2 \times f_0)$ = sum of the outputs. [5] Feedback current is included in the C_{PD}.

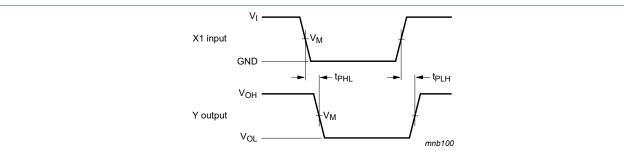
11.1. Waveforms and test circuit



Measurement points are given in <u>Table 9</u>.

Logic levels: V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig. 5. The input (X1) to output (X2) propagation delays



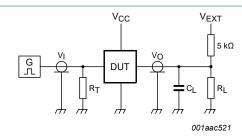
Measurement points are given in Table 9.

Logic levels: V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig. 6. The input (X1) to output (Y) propagation delays

Table 9. Measurement points

Supply voltage	Output	Input					
V _{CC}	V _M	V _M	VI	$t_r = t_f$			
0.8 V to 3.6 V	0.5 × V _{CC}	0.5 × V _{CC}	V _{CC}	≤ 3.0 ns			



Test data is given in Table 10.

Definitions for test circuit:

R_L = Load resistance;

C_L = Load capacitance including jig and probe capacitance;

 R_T = Termination resistance should be equal to the output impedance Z_0 of the pulse generator;

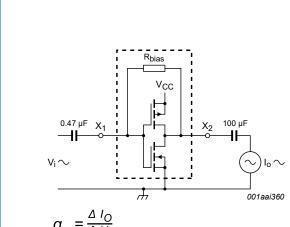
V_{EXT} = External voltage for measuring switching times.

Fig. 7. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Load		V _{EXT}			
V _{CC}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}	
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	2 × V _{CC}	

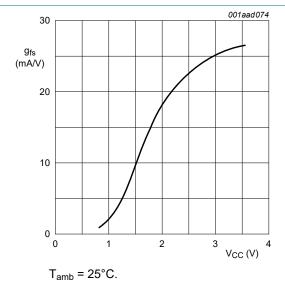
[1] For measuring enable and disable times R_L = 5 k Ω . For measuring propagation delays, setup and hold times and pulse width R_L = 1 M Ω .



 $g_{fs} = \frac{\Delta I_O}{\Delta V_I}$ f_i = 1 kHz.

Vo is constant.

Fig. 8. Test set-up for measuring forward transconductance



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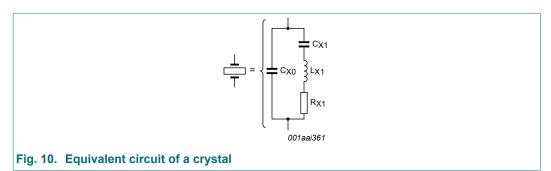
12. Application information

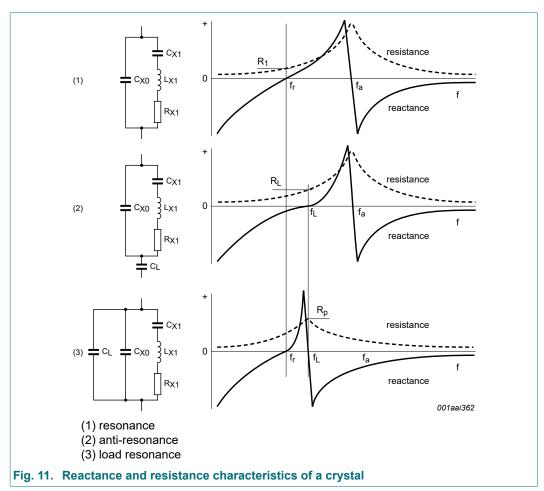
Crystal controlled oscillator circuits are widely used in clock pulse generators because of their excellent frequency stability and wide operating frequency range. The use of the 74AUP1Z04-Q100 provides the additional advantages of low power dissipation, stable operation over a wide range of frequency and temperature and a very small footprint. This application information describes crystal characteristics, design and testing of crystal oscillator circuits based on the 74AUP1Z04-Q100.

12.1. Crystal characteristics

Fig. 10 is the equivalent circuit of a quartz crystal.

The reactive and resistive component of the impedance of the crystal alone and the crystal with a series and a parallel capacitance is shown in Fig. 11.





12.1.1. Design

Fig. 12 shows the recommended way to connect a crystal to the 74AUP1Z04-Q100. This circuit is basically a Pierce oscillator circuit in which the crystal is operating at its fundamental frequency and is tuned by the parallel load capacitance of C_1 and C_2 . C_1 and C_2 are in series with the crystal. They should be approximately equal. R_1 is the drive-limiting resistor and is set to approximately the same value as the reactance of C_1 at the crystal frequency ($R_1 = X_{C_1}$). This will result in an input to the crystal of 50 % of the rail-to-rail output of X2. This keeps the drive level into the crystal within drive specifications (the designer should verify this). Overdriving the crystal can cause damage.

The internal bias resistor provides negative feedback and sets a bias point of the inverter near mid-supply, operating the 74AUP1GU04-Q100 portion in the high gain linear region.

To calculate the values of C₁ and C₂, the designer can use the formula:

$$C_L = \frac{C_1 \times C_2}{C_1 + C_2} + C_s$$

 C_L is the load capacitance as specified by the crystal manufacturer, C_s is the stray capacitance of the circuit (for the 74AUP1Z04-Q100 this is equal to an input capacitance of 1.5 pF).

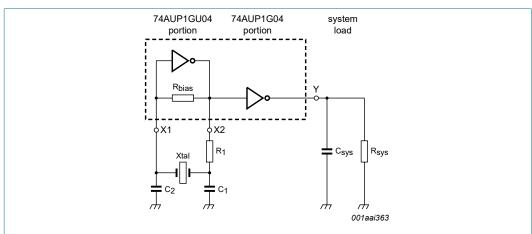


Fig. 12. Crystal oscillator configuration for the 74AUP1Z04-Q100

12.1.2. **Testing**

After the calculations are performed for a particular crystal, the oscillator circuit should be tested. The following simple checks will verify the prototype design of a crystal controlled oscillator circuit. Perform them after laying out the board:

- Test the oscillator over worst-case conditions (lowest supply voltage, worst-case crystal and highest operating temperature). Adding series and parallel resistors can simulate a worst-case crystal.
- Insure that the circuit does not oscillate without the crystal.
- Check the frequency stability over a supply range greater than that which is likely to occur during normal operation.
- Check that the start-up time is within system requirements.

As the 74AUP1Z04-Q100 isolates the system loading, once the design is optimized, the single layout may work in multiple applications for any given crystal.

13. Package outline

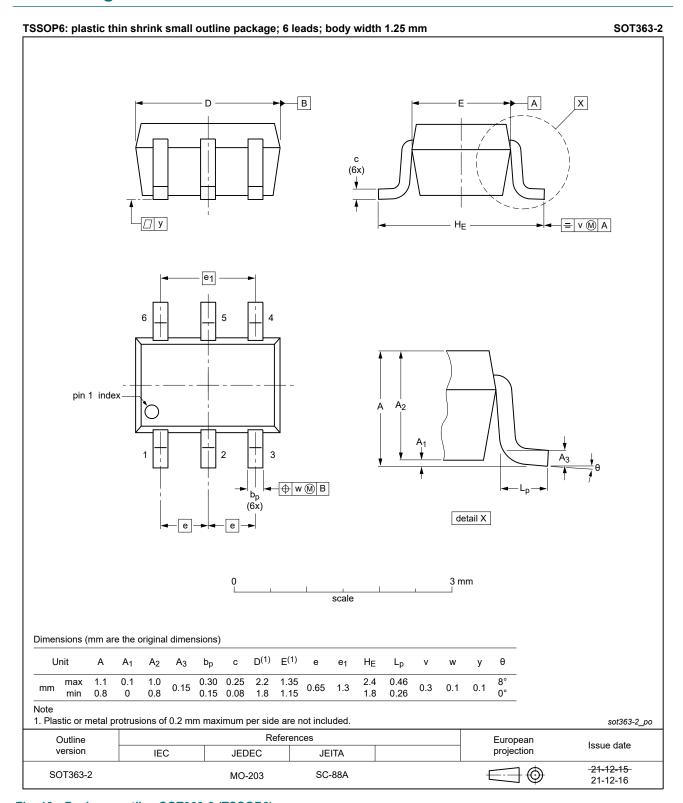


Fig. 13. Package outline SOT363-2 (TSSOP6)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

15. Revision history

Table 12. Revision history

,						
Document ID	Release date	Data sheet status	Change notice	Supersedes		
74AUP1Z04_Q100 v.2	20220127	Product data sheet	-	74AUP1Z04_Q100 v.1		
Modifications	SOT363 (SC-88) package changed to SOT363-2 (TSSOP6) package.					
74AUP1Z04_Q100 v.1	20200818	Product data sheet	-	-		

16. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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